## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No
Filing Date July 13, 2001
Inventor
Assignee Micron Technology, Inc.
Group Art Unit
Examiner
Attorney's Docket No
Title: Chemical Vapor Deposition Methods of Forming Barium Strontium
Titanate Comprising Dielectric Layers, Including Such Layers Having a
Varied Concentration of Barium and Strontium Within the Layer

## RESPONSE TO DECEMBER 19, 2001 OFFICE ACTION

To:

Box Non-Fee Amendment

Assistant Commissioner for Patents

Washington, D.C. 20231

VIA EXPRESS MAIL

From:

Mark S. Matkin (Tel. 509-624-4276; Fax 509-838-3424)

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Responsive to the Office Action dated December 19, 2001, Applicant amends and remarks as follows:

## **AMENDMENTS**

## In the Specification

Please replace the paragraph beginning at line 6 on page 19 with the following clean replacement paragraph in accordance with 37 § 1.121(b)(1)(ii). A marked-up version showing amendments to the ARECEIVED

1 MAR 18 2002

1 VO specification paragraph being changed is provided in one or more

MI221657.M01

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